



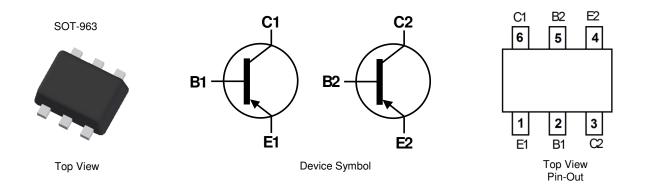
45V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT-963

Features

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Complementary NPN Type Available (DST847BDJ)
- Ultra Small Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.0027 grams (Approximate)



Ordering Information

Device	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DST857BDJ-7	Standard	TB	7	8	10,000

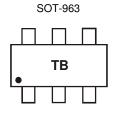
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



TB = Product Type Marking Code



Absolute Maximum Rating (@T_A = +25 °C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 5)	lc	-100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	C

Note: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.

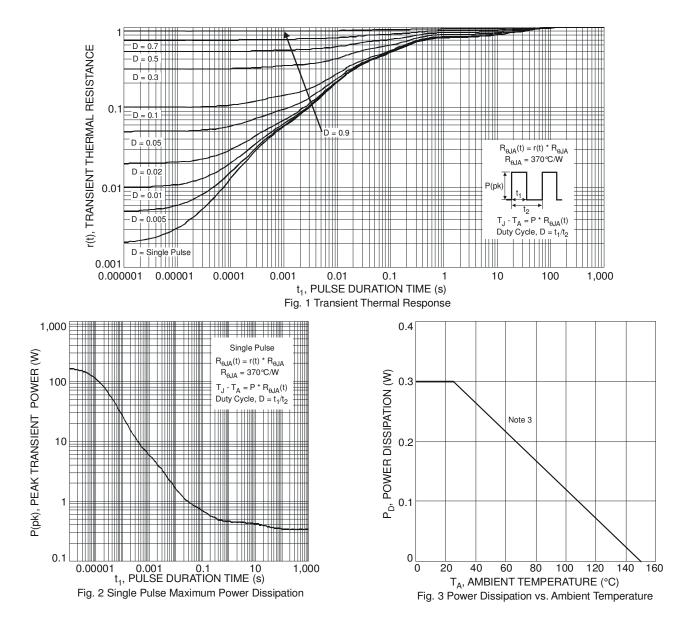
ESD rating

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Note: 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

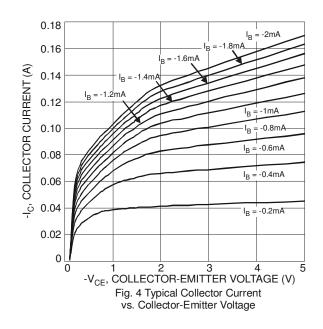


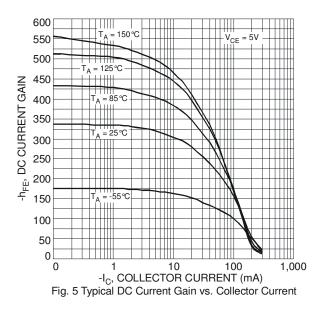


Typical Electrical Characteristics (@T_A = +25 °C unless otherwise specified.)

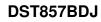
Characteristic (Note 7)	Symbol	Min	Typical	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-50	-100	-	V	$I_{\rm C} = -10 \mu A$, $I_{\rm B} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	-50	-90	-	V	$I_{\rm C} = -10 \mu A, I_{\rm B} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-45	-65	-	V	$I_{C} = -1mA, I_{B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-6	-8.5	-	V	$I_{E} = -1\mu A, I_{C} = 0$
Collector Cut-Off Current	I _{CBO}	-	-	-15	nA	V _{CB} = -30V
DC Current Gain	h _{FE}	- 200	340 330	- 470	-	$I_{C} = -10\mu A$, $V_{CE} = -5V$ $I_{C} = -2.0mA$, $V_{CE} = -5V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-70 -300	-175 -500	mV	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		-760 -885	-1,000 -1,100	mV	$I_{C} = -10mA$, $I_{B} = -0.5mA$ $I_{C} = -100mA$, $I_{B} = -5.0mA$
Base-Emitter Voltage	V _{BE(on)}	-600	-670 -715	-780 -850	mV	$I_{C} = -2.0 \text{mA}, V_{CE} = -5 \text{V}$ $I_{C} = -10 \text{mA}, V_{CE} = -5 \text{V}$
Current Gain-Bandwidth Product	f⊤	100	340	-	MHz	$V_{CE} = -5V$, $I_C = -10mA$, f = 100MHz
Output Capacitance	C _{obo}	-	2.0	-	pF	V _{CB} = -10V, f = 1.0MHz

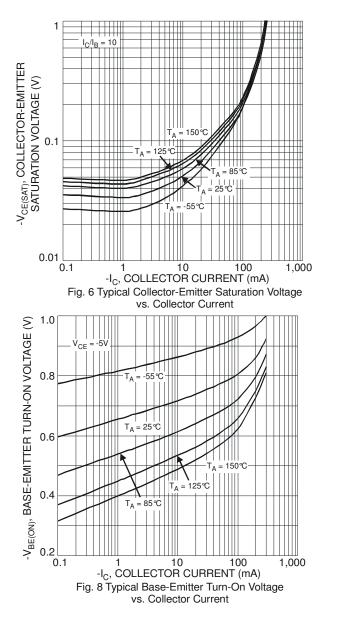
Note: 7. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%.

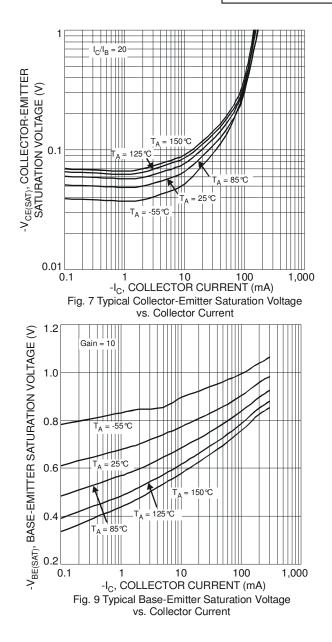








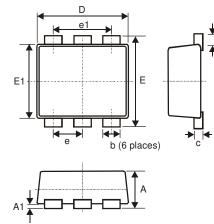






Package Outline Dimensions

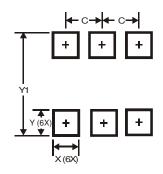
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT-963					
Dim	Min	Max	Тур		
Α	0.40	0.50	0.45		
A1	0	0.05	-		
С	0.120	0.180	0.150		
D	0.95	0.95 1.05 1.00			
Е	0.95	1.05	1.00		
E1	0.75 0.85 0.80				
L	0.05 0.15 0.10				
b	0.10 0.20 0.15				
е	0.35 Typ				
e1	0.70 Тур				
All Dimensions in mm					

Suggest Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.350		
Х	0.200		
Y	0.200		
Y1	1.100		



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